

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Vishay/Siliconix DG2018DN-T1-E4

For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>





DG2018, DG2019

Vishay Siliconix

Low Voltage, Dual DPDT and Quad SPDT Analog Switches

DESCRIPTION

The DG2018 and DG2019 are low voltage, single supply analog switches. The DG2018 is a dual double-pole/doublethrow (DPDT) with two control inputs that each controls a pair of single-pole/double-throw (SPDT). The DG2019 uses one control pin to operate four independent SPDT switches.

When operated on a + 3 V supply, the DG2018's control pins are compatible with 1.8 V digital logic. The DG2019 has an available feature of a V_L pin that allows a 1.0 V threshold for the control pin when V_L is powered with 1.5 V.

Built on Vishay Siliconix's low voltage submicron CMOS process, the DG2018 and DG2019 are ideal for high performance switching of analog signals; providing low on-resistance (6 Ω at + 2.7 V), fast speed (T_{on}, T_{off} at 42 ns and 16 ns), and a bandwidth that exceeds 180 MHz.

The DG2018 and DG2019 were designed to offer solutions that extend beyond audio/video functions, to providing the performance required for today's demanding mixed-signal switching in portable applications.

An epitaxial layer prevents latch-up. Brake-before-make is guaranteed for all SPDT's. All switches conduct equally well in both directions when on, and blocks up to the power supply level when off.

FEATURES

- Low voltage operation (1.8 V to 5.5 V)
- Low on resistance
 - R_{DS(on)}: 6 Ω at 2.7 V
- Low voltage logic compatible
 DG2019: V_{INH} = 1 V
- High bandwidth: 180 MHz
- QFN-16 package

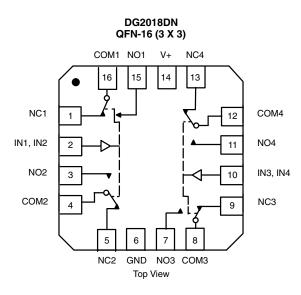
BENEFITS

- Ideal for both analog and digital signal switching
- Reduced power consumption
- High accuracy
- Reduced PCB space
- · Fast switching
- Low leakage

APPLICATIONS

- Cellular phones
- Audio and video signal routing
- PCMCIA cards
- Battery operated systems
- Portable instrumentation

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE										
IN1, IN2										
Logic	NC1 and NC2	NO1 and NO2								
0	ON	OFF								
1	OFF ON									
IN3, IN4										
Logic	Logic NC3 and NC4 NO3 and NO4									
0	ON	OFF								
1	OFF	ON								

ORDERING INFORMATION								
Temp. Range	Temp. Range Package Part Number							
- 40 °C to 85 °C	QFN-16 (3 x 3 mm)	DG2018DN						

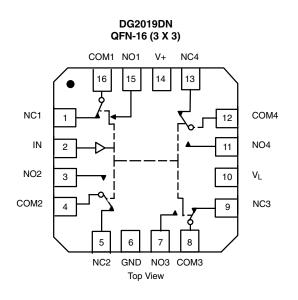


DG2018, DG2019

Vishay Siliconix



FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE									
Logic	Logic NC1, 2, 3 and 4 NO1, 2								
0	ON	OFF							
1	OFF	ON							

ORDERING INFORMATION									
Temp. Range	p. Range Package Part Number								
- 40 °C to 85 °C	QFN-16 (3 x 3 mm)	DG2019DN							

ABSOLUTE MAXIMUM RATINGS									
Parameter		Limit	Unit						
Reference V+ to GND	- 0.3 to + 6	V							
IN, COM, NC, NO		- 0.3 to (V+ + 0.3)							
Continuous Current (Any terminal)		± 50	mA						
Peak Current (Pulsed at 1 ms, 10 % Duty Cy	cle)	± 100							
Storage Temperature (D Suffix)		- 65 to 150	°C						
Power Dissipation (Packages) ^b	QFN-16 (3 x 3 mm) ^c	850	mW						

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 4.0 mW/°C above 70 °C.





DG2018, DG2019

Vishay Siliconix

Analog Switch Analog Signal Range ^d V _N Analog Signal Range ^d V On-Resistance I R _{ON} Flatness FI R _{ON} Match Between Z Channels I Switch Off Leakage Current I Digital Control I Input High Voltage I	Symbol NO, V _{NC} , V _{COM} R _{ON} R _{ON} latness ΔR _{ON} NO(off) NO(off) NC(off) COM(off)	V+ = 3 V, ± 10 %, (DG2018 Only) V _{IN} = 0.5 or 1. (DG2019 Only) V _L = 1.5 V, V _{IN} = 0.4 V+ = 2.7 V, V _{COM} = 0.2 V/1.5 I _{NO} , I _{NC} = 10 mA V+ = 2.7 V V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10	4 or 1.0 V ^e	Temp. ^a Full Room Full Room	Min.^b	Тур.^с	Max. ^b	Unit V	
Analog Switch Analog Signal Range ^d V _N Analog Signal Range ^d V On-Resistance I R _{ON} Flatness FI R _{ON} Match Between 2 Channels I Switch Off Leakage Current I Digital Control I Input High Voltage I	NO, V _{NC} , V _{COM} R _{ON} latness ΔR _{ON} NO(off) NO(off)	(DG2019 Only) $V_L = 1.5 \text{ V}, V_{IN} = 0.4$ $V_{+} = 2.7 \text{ V}, V_{COM} = 0.2 \text{ V}/1.5$ $I_{NO}, I_{NC} = 10 \text{ mA}$ $V_{+} = 2.7 \text{ V}$ $V_{COM} = 0 \text{ to } V_{+}, I_{NO}, I_{NC} = 10$	4 or 1.0 V ^e	Full Room Full			V+ 12		
Analog Switch Analog Signal Range ^d V _N Analog Signal Range ^d V On-Resistance I R _{ON} Flatness FI R _{ON} Match Between 2 Channels I Switch Off Leakage Current I Digital Control I Input High Voltage I	NO, V _{NC} , V _{COM} R _{ON} latness ΔR _{ON} NO(off) NO(off)	V+ = 2.7 V, V _{COM} = 0.2 V/1.5 I _{NO} , I _{NC} = 10 mA V+ = 2.7 V V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10	5 V	Full Room Full			V+ 12		
Analog Signal Range ^d V _N On-Resistance I R _{ON} Flatness FI R _{ON} Match Between I Channels I Switch Off Leakage Current I Channel-On Leakage Current I Digital Control I Input High Voltage I	V _{COM} R _{ON} R _{ON} latness ΔR _{ON}	I_{NO} , $I_{NC} = 10 \text{ mA}$ V+ = 2.7 V V _{COM} = 0 to V+, I_{NO} , $I_{NC} = 10$		Room Full	0	6	12	V	
On-Resistance Image: Constraint of the second sec	R _{ON} R _{ON} latness ΔR _{ON}	I_{NO} , $I_{NC} = 10 \text{ mA}$ V+ = 2.7 V V _{COM} = 0 to V+, I_{NO} , $I_{NC} = 10$		Full		6			
Hon Frainess FI R _{ON} Match Between 2 Channels 1 Switch Off Leakage Current 1 Input High Voltage 1	Iatness ∆R _{ON} NO(off) NC(off)	$V_{COM} = 0$ to V+, I_{NO} , $I_{NC} = 10$	mA	Room			15	l	
Channels I Switch Off Leakage Current I I I Channel-On Leakage Current I Digital Control I Input High Voltage I	NO(off) NC(off)		mA	1		0.5	2	Ω	
Switch Off Leakage Current Index Index Channel-On Leakage Current Index Digital Control Index Input High Voltage Index	I _{NC(off)}								
Ic Ic Channel-On Leakage Current Ic Digital Control Input High Voltage		$v + = 3.3 v, v_{NO}, v_{NC} = 0.3 v/$	V+ = 3.3 V, V _{NO} , V _{NC} = 0.3 V/3 V		- 1 - 10	0.3	1 10	nA	
Digital Control Input High Voltage		V _{COM} = 3 V/0.3 V	Room Full	- 1 - 10	0.3	1 10			
Input High Voltage	COM(on)	V + = 3.3 V, V_{NO} , V_{NC} = V_{COM} = 0.	Room Full	- 1 10	0.3	1 10			
	<u> </u>								
	V _{INH}		DG2018	Full	1.4				
Input Low Voltage		V _L = 1.5 V	DG2019	Full	1.0		0.5	. v	
pat zon ronago	V _{INL}	V ₁ = 1.5 V	DG2018 DG2019	Full Full			0.5 0.4		
Input Capacitance	C _{in}	f = 1 MHz	D02019	Full		9	0.4	pF	
	L or I _{INH}	V _{IN} = 0 or V+		Full	- 1	Ŭ	1	μΑ	
Dynamic Characteristics				i un	•		-	μπ	
	t _{ON}			Room Full		42	55 65		
Turn-Off Time	t _{OFF}	$V_{NO} \text{ or } V_{NC}$ = 2.0 V, R _L = 300 Ω , C _I	L = 35 p⊢	Room Full		16	25 35	ns	
Break-Before-Make Time	t _d	$V_{\rm NO}$ or $V_{\rm NC}$ = 2.0 V, R _L = 50 Ω, C _L	= 35 pF	Full	1				
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, R_{GEN} =$: 0 Ω	Room		- 1.46		рС	
Off-Isolation ^d	OIRR			Room		- 67			
	X _{TALK}	R_L = 50 Ω, C_L = 5 pF, f = 1 M	Hz	Room		- 72		dB	
Bandwidth ^d	BW			Room		180		MHz	
0	C _{NO(off)}			Room		9			
No No Off Capacitance	C _{NC(off)}			Room		9		~ -	
С	NO(on)	$V_{IN} = 0$ or V+, f = 1 MHz		Room		30		pF	
	C _{NC(on}			Room		30		1	
Power Supply		V _{IN} = 0 or V+							

Notes:

a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.



DG2018, DG2019

Vishay Siliconix



SPECIFICATIONS V+ =	= 5 V							
		Test Conditions Otherwise Unless Specif V+ = 5 V, ± 10 %,		- 4(Limits) °C to 85	°C		
		(DG2018 Only) V _{IN} = 0.8 or 1	I.8 V ^e					
Parameter	Symbol	(DG2019 Only) V _L = 1.5 V, V _{IN} = 0		Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch							1	
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V	
On-Resistance	R _{ON}	V+ = 4.5 V, V _{COM} = 3 V, I _{NO} , I _{NC}	Room Full		4	8 10		
R _{ON} Flatness	R _{ON} Flatness	V+ = 4.5 V V _{COM} = 0 to V+, I _{NO} , I _{NC} = 1	Room		0.6	1.2	Ω	
R _{ON} Match Between Channels	ΔR_{ON}	$V_{COM} = 0.00 V_{+}, I_{NO}, I_{NC} = 1$	UIIA	Room		0.6	1.2	
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 5.5 V		Room Full	- 1 - 10	0.03	1 10	
Switch On Leakage Guneni	I _{COM(off)}	V _{NO} , V _{NC} = 1 V/4.5 V, V _{COM} = 4	$V_{NO}, V_{NC} = 1 \text{ V/4.5 V}, V_{COM} = 4.5 \text{ V/1 V}$		- 1 - 10	0.03	1 10	nA
Channel-On Leakage Current ^f	I _{COM(on)}	V + = 5.5 V, V_{NO} , V_{NC} = V_{COM} =	Room Full	- 1 - 10	0.03	1 10		
Digital Control		1	1					
Input High Voltage	V _{INH}	V _L = 1.5 V	DG2018 DG2019	Full Full	1.8 1.0			V
Input Low Voltage	V _{INL}		DG2018	Full			0.8	V
Input Low Voltage	V INL	$V_{L} = 1.5 V$	DG2019	Full			0.4	
Input Capacitance	C _{in}			Full		9		pF
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	V _{IN} = 0 or V+		Full	1		1	μA
Dynamic Characteristics	1			1		1	1	-
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 3 V, R _L = 300 Ω, C	1 = 35 pF	Room Full		44	48 52	
Turn-Off Time	t _{OFF}			Room Full		19	33 35	ns
Break-Before-Make Time	t _d	$V_{NO} \text{ or } V_{NC} = 3 \text{ V}, \text{ R}_{L} = 50 \Omega, \text{ C}_{L}$		Full	1			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, \text{ R}_{GEN}$	= 0 Ω	Room		- 2.46		рС
Off-Isolation ^d	OIRR			Room		- 67		dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \ \Omega$, $C_L = 5 \ pF$, f = 1 I	MHz	Room		- 72		
Bandwidth ^d	BW			Room		180		MHz
Source-Off Capacitance ^d	C _{NO(off)}			Room		7.5		
	C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	z	Room		7.5		pF
Channel-On Capacitance ^d	C _{NO(on)}	in,-	Room		30		יק	
	C _{NC(on}		Room		30			
Power Supply	1					1		
Power Supply Range Power Supply Current	V+			Full	1.8	0.01	5.5 1.0	V
Power Supply Current	I+	$v_{\rm IN} = 0$ or $v_{\rm H}$	V _{IN} = 0 or V+					μA

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

f. Not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





DG2018, DG2019

4

5

8 M

I_{COM(on)}

2.5

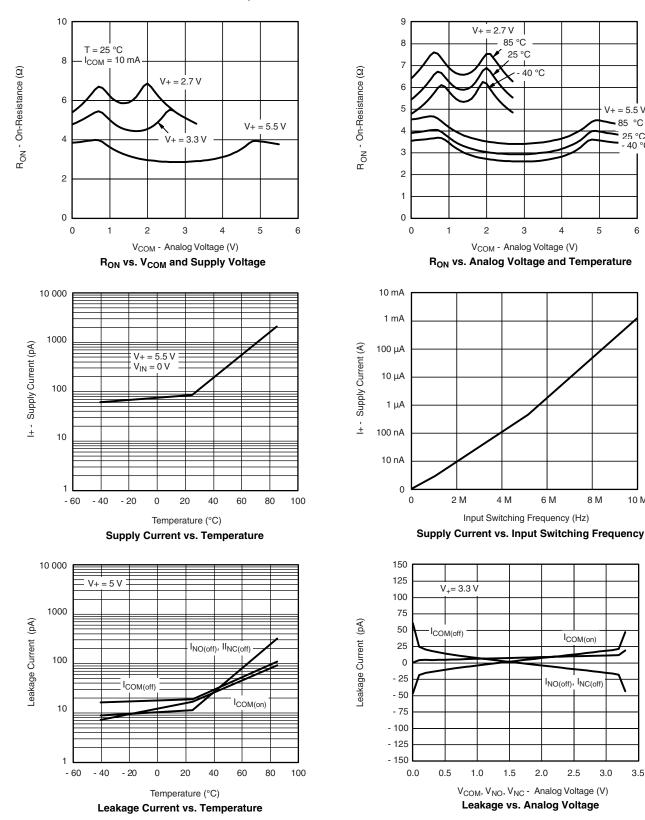
10 M

Vishay Siliconix

V+ = 5.5 V •85 °C

25 °C - 40 °C

6



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Document Number: 72342 S-82626-Rev. C, 03-Nov-08 3.0

3.5

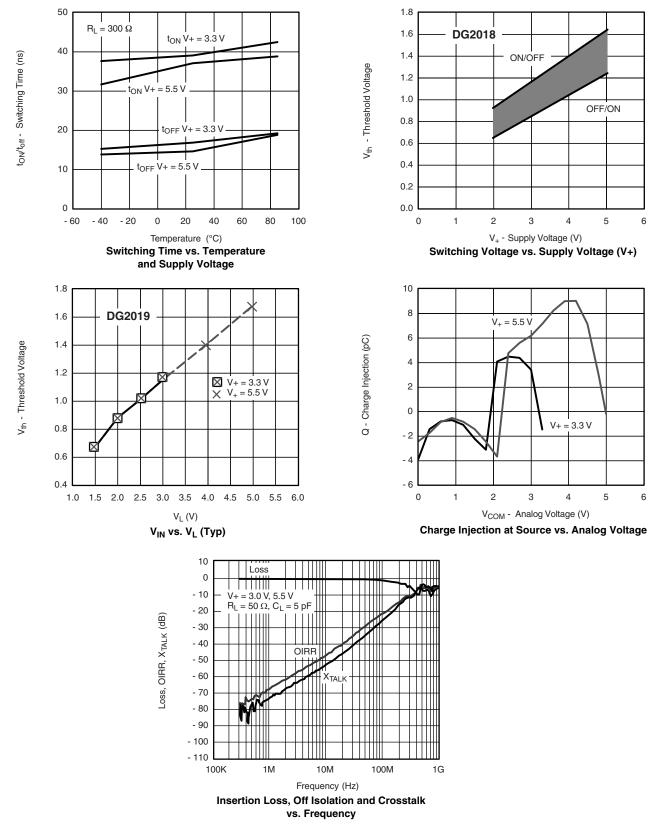


DG2018, DG2019

Vishay Siliconix



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



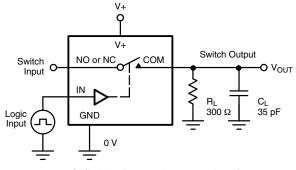


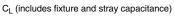
VISHAY.

DG2018, DG2019

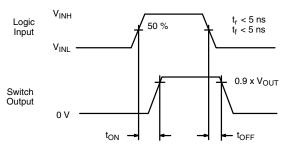
Vishay Siliconix

TEST CIRCUITS



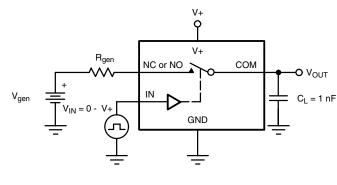


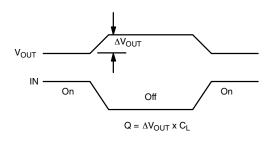
$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



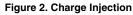
Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

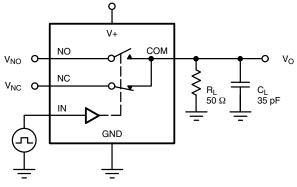


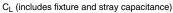




IN depends on switch configuration: input polarity determined by sense of switch.







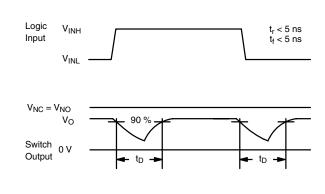


Figure 3. Break-Before-Make Interval



DG2018, DG2019

Vishay Siliconix



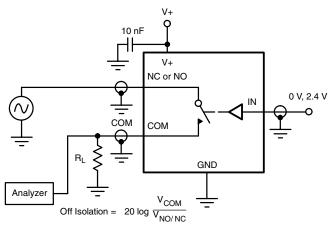


Figure 4. Off-Isolation

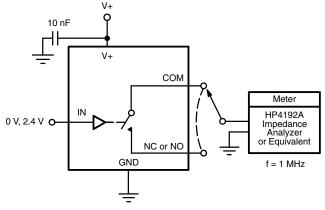


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72342.

VISHAY

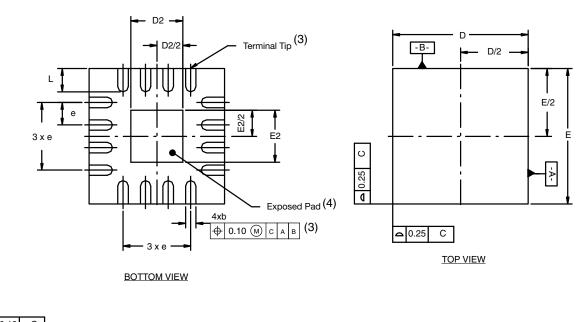


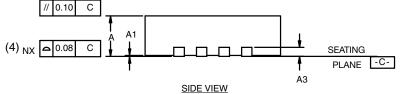


Package Information

Vishay Siliconix

QFN-16 Lead (3 x 3)





Notes

⁽¹⁾ All dimensions are in millimeters.

⁽²⁾ N is the total number of terminals.

⁽³⁾ Dimension b applies to metallized terminal and is measured between 0.25 and 0.30 mm from terminal tip.

⁽⁴⁾ Coplanarity applies to the exposed heat sink slug as well as the terminal.

⁽⁵⁾ The pin #1 identifier may be either a mold or marked feature, it must be located within the zone indicated.

			VARIA	TION 1		VARIATION 2						
DIM.	MILLIMETERS		MILLIMETERS INCHES			MILLIMETERS			INCHES			
	MIN.	NOM	MAX.	MIN.	NOM	MAX.	MIN.	NOM	MAX.	MIN.	NOM	MAX.
А	0.80	0.90	1.00	0.031	0.035	0.039	0.80	0.90	1.00	0.031	0.035	0.039
b	0.18	0.23	0.30	0.007	0.009	0.012	0.18	0.25	0.30	0.007	0.010	0.012
D	2.90	3.00	3.10	0.114	0.118	0.122	2.90	3.00	3.10	0.114	0.118	0.122
D2	1.00	1.15	1.25	0.039	0.045	0.049	1.50	1.70	1.80	0.059	0.067	0.071
E	2.90	3.00	3.10	0.114	0.118	0.122	2.90	3.00	3.10	0.114	0.118	0.122
E2	1.00	1.15	1.25	0.039	0.045	0.049	1.50	1.70	1.80	0.059	0.067	0.071
е	e 0.50 BSC			0.50 BSC 0.020 BSC				0.50 BSC			0.020 BSC	;
L	0.30	0.40	0.50	0.012	0.016	0.020	0.30	0.40	0.50	0.012	0.016	0.020
ECN: T16-0233 DWG: 5899	ECN: T16-0233-Rev. D, 09-May-16 DWG: 5899											

Revision: 09-May-16





www.vishay.com

Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.